

具有 $\pm 15\text{kV}$ ESD 保护功能的 3V 至 5.5V 多通道 RS-232 线路驱动器和接收器

1 特性

- 为 RS-232 总线引脚提供 ESD 保护
 - $\pm 15\text{kV}$ 人体放电模型 (HBM)
 - $\pm 8\text{kV}$ IEC 61000-4-2 接触放电
 - $\pm 15\text{kV}$ IEC 61000-4-2 气隙放电
- 符合或超出 TIA/EIA-232-F 和 ITU v.28 标准的要求
- 由 3V 至 5.5V V_{CC} 电源供电
- 速率高达 1000kbit/s
- 两个驱动器和两个接收器
- 低待机电流。..1 μA (典型值)
- 外部电容器 $4 \times 0.1 \mu\text{F}$
- 接受 5V 逻辑输入及 3.3V 电源

2 应用

- 工业 PC
- 有线网络
- 数据中心和网络设备
- 笔记本电脑
- 手持设备

3 说明

SN65C3222E 和 SN75C3222E 由两个线路驱动器、两个线路接收器和一个双路电荷泵电路组成，具有引脚

对引脚 (串行端口连接引脚，包括 GND) $\pm 15\text{kV}$ ESD 保护。

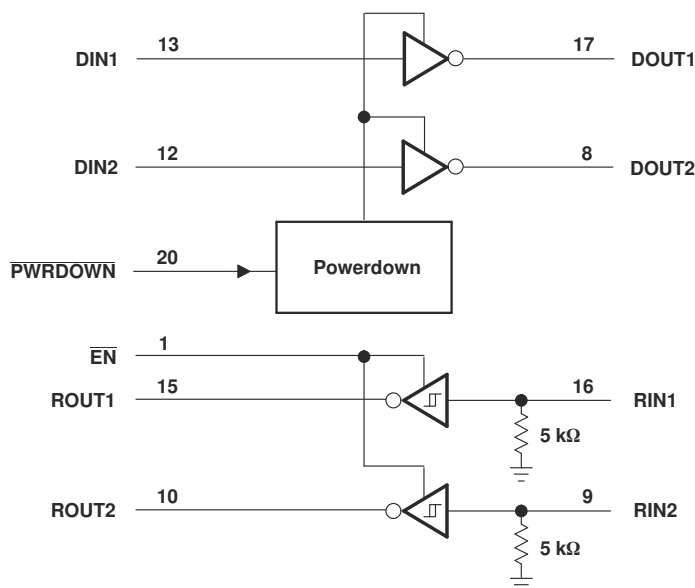
这两款器件均符合 TIA/EIA-232-F 的要求并在异步通信控制器与串行端口连接器之间提供电气接口。电荷泵和四个小型外部电容器支持由 3V 至 5.5V 单电源供电。这些器件以高达 1000kbit/s 的典型数据信号传输速率运行，是对业界常用的 3222 两驱动器、两接收器功能进行改进后的直接可替代产品。

通过设置关断 ($\overline{\text{PWRDOWN}}$) 输入低电平 (仅从电源消耗 1 μA 电流)，可以将 SN65C3222E 和 SN75C3222E 置于关断模式。当器件关断时，接收器保持活动状态，而驱动器置于高阻抗状态。此外，在关断期间，将会禁用板载电荷泵； V_+ 降低至 V_{CC} ， V_- 升高至 GND。通过将启用 ($\overline{\text{EN}}$) 设置为高电平，接收器输出也可以置于高阻抗状态。

器件信息

器件型号	封装 ⁽¹⁾	封装尺寸 (标称值)
SN65C3222E SN75C3222E	DB (SSOP) (20)	10.2 mm x 5.30 mm
	DW (SOIC) (20)	15.4mm x 7.50mm
	PW (TSSOP) (20)	7.80 mm x 4.40mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。



引脚编号用于 DB、DW 和 PW 封装。

逻辑图 (正逻辑)



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4 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision A (July 2006) to Revision B (August 2021)	Page
• 更新了 <i>应用</i> 部分的列表。.....	1
• 删除了 <i>订购信息</i> 表。从 <i>器件信息</i> 表中删除了 RHL 封装。.....	1
• 添加了 <i>器件信息</i> 表、 <i>引脚配置和功能</i> 、 <i>详细说明</i> 部分、 <i>应用和</i> <i>实施</i> 部分.....	1
• Deleted the Package thermal impedance from the <i>Absolute Maximum Ratings</i>4	4
• Added the <i>ESD Ratings</i> table.....4	4
• Added the <i>Thermal Information: SN65C3222E</i> table.....5	5
• Changed the value of $R_{\theta JA}$ for PW package (previously in the <i>Absolute Maximum Ratings</i> table), and added additional thermal parameters for all packages in the <i>Thermal Information: SN65C3222E</i> table.....5	5
• Added separate <i>Thermal Information</i> table for SN75C3222E.....5	5

5 Pin Configuration and Functions

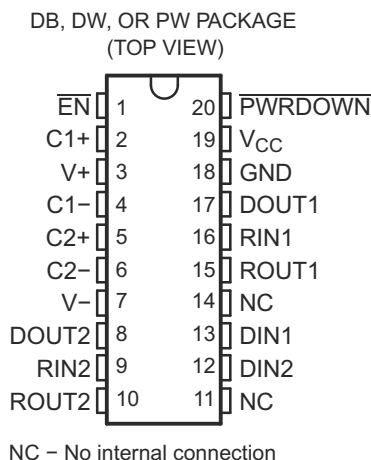


表 5-1. Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
C1+	2	—	Charge pump capacitor pin
C1-	4	—	Charge pump capacitor pin
C2+	5	—	Charge pump capacitor pin
C2-	6	—	Charge pump capacitor pin
DIN1	13	I	Driver logic input
DIN2	12	I	Driver logic input
DOUT1	17	O	RS-232 driver output
DOUT2	8	O	RS-232 driver output
EN	1	I	Receiver enable, active low
GND	18	—	Ground
NC	11,14	—	No internal connection
PWRDOWN	20	I	Driver disable, active low
RIN1	16	I	RS-232 receiver input
RIN2	9	I	RS-232 receiver input
ROUT1	15	O	Receiver logic output
ROUT2	10	O	Receiver logic output
V _{CC}	19	—	Power Supply
V+	3	—	Charge pump capacitor pin
V-	7	—	Charge pump capacitor pin

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) ⁽¹⁾

			MIN	MAX	UNIT
V _{CC}	Supply voltage range ⁽²⁾		- 0.3	6	V
V+	Positive-output supply voltage range ⁽²⁾		- 0.3	7	V
V-	Negative-output supply voltage range ⁽²⁾		0.3	- 7	V
V+ - V-	Supply voltage difference ⁽²⁾			13	V
V _I	Input voltage range	Driver (EN, PWRDOWN)	- 0.3	6	V
		Receiver	- 25	25	
V _O	Output voltage range	Driver	- 13.2	13.2	V
		Receiver	- 0.3	V _{CC} + 0.3	
T _J	Operating virtual junction temperature			150	°C
T _{stg}	Storage temperature range		- 65	150	°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltages are with respect to network GND.

6.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±3,000	V
		RIN1, RIN2, DOUT1 and DOUT2 pins to GND	±15,000	
		Charged device model (CDM), per ANSI/ESDA/JEDEC JS-002 ⁽²⁾	±1,500	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 ESD Ratings - IEC Specifications

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	IEC 61000-4-2, Contact Discharge ⁽¹⁾	±8,000	V
		IEC 61000-4-2, Air Discharge ⁽¹⁾	±15,000	

(1) For the PW Package of SN65C3222E only, a minimum of 1-μF capacitor is required between V_{CC} and GND to meet the specified IEC 61000-4-2 rating

6.4 Recommended Operating Conditions

See 图 9-1 and (1)

				MIN	NOM	MAX	UNIT
Supply voltage			V _{CC} = 3.3 V	3	3.3	3.6	V
			V _{CC} = 5 V	4.5	5	5.5	
V _{IH}	Driver and control high-level input voltage	DIN, EN, PWRDOWN	V _{CC} = 3.3 V	2			V
			V _{CC} = 5 V	2.4			
V _{IL}	Driver and control low-level input voltage	DIN, EN, PWRDOWN				0.8	V
V _I	Driver and control input voltage	DIN, EN, PWRDOWN		0		5.5	V
V _I	Receiver input voltage			− 25		25	V
T _A	Operating free-air temperature		SN75C3222E	0		70	°C
			SN65C3222E	− 40		85	

(1) Test conditions are C1 – C4 = 0.1 μF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μF, C2 – C4 = 0.33 μF at V_{CC} = 5 V ± 0.5 V.

6.5 Thermal Information: SN65C3222E

THERMAL METRIC ⁽¹⁾		SN65C3222E			UNIT
		DB (SSOP)	DW (SOIC)	PW (TSSOP)	
		20 Pins	20 Pins	20 Pins	
R _{θJA}	Junction-to-ambient thermal resistance	70	58	94.1	°C/W
R _{θJC(top)}	Junction-to-case (bottom) thermal resistance	33.6	30.0	35.2	°C/W
R _{θJB}	Junction-to-board thermal resistance	36.4	29.6	45.5	°C/W
ψ _{JT}	Junction-to-top characterization parameter	4.8	7.7	3.1	°C/W
ψ _{JB}	Junction-to-board characterization parameter	35.9	29.3	45.1	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC package thermal metrics](#) application report.

6.6 Thermal Information: SN75C3222E

THERMAL METRIC ¹		SN75C3222E			UNIT
		DB (SSOP)	DW (SOIC)	PW (TSSOP)	
		20	20	20	
R _{θJA}	Junction-to-ambient thermal resistance	70	58	83	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	33.6	30.0	24.8	°C/W
R _{θJB}	Junction-to-board thermal resistance	36.4	29.6	39.5	°C/W
ψ _{JT}	Junction-to-top characterization parameter	4.8	7.7	1.1	°C/W
ψ _{JB}	Junction-to-board characterization parameter	35.9	29.3	39.0	°C/W

6.7 Electrical Characteristics

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see 图 9-1)

PARAMETER		TEST CONDITIONS ⁽²⁾	MIN	TYP ⁽¹⁾	MAX	UNIT
I _I	Input leakage current (EN, PWRDOWN)			±0.01	±1	μA
I _{CC}	Supply current	No load, PWRDOWN at V _{CC}		0.3	1	mA
	Supply current (powered off)	No load, PWRDOWN at GND		1	10	μA

(1) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

(2) Test conditions are C1 – C4 = 0.1 μF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μF, C2 – C4 = 0.33 μF at V_{CC} = 5 V ± 0.5 V.

6.8 Electrical Characteristics: Driver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see [Figure 9-1](#))

PARAMETER	TEST CONDITIONS	MIN	TYP ⁽¹⁾ (3)	MAX	UNIT
V _{OH} High-level output voltage	DOUT at R _L = 3 kΩ to GND, DIN = GND	5	5.4		V
V _{OL} Low-level output voltage	DOUT at R _L = 3 kΩ to GND, DIN = V _{CC}	- 5	- 5.4		V
I _{IH} High-level input current	V _I = V _{CC}		±0.01	±1	μA
I _{IL} Low-level input current	V _I at GND		±0.01	±1	μA
I _{OS} Short-circuit output current ⁽²⁾	V _{CC} = 3.6 V	V _O = 0 V	±35	±60	mA
	V _{CC} = 5.5 V				
r _o Output resistance	V _{CC} , V ₊ , and V ₋ = 0 V, V _O = ±2 V	300	10M		Ω
I _{OZ} Output leakage current	PWRDOWN = GND	V _{CC} = 3 V to 3.6 V, V _O = ±12 V		±25	μA
		V _{CC} = 4.5 V to 5.5 V, V _O = ±10 V		±25	

(1) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

(2) Short-circuit durations should be controlled to prevent exceeding the device absolute power dissipation ratings, and not more than one output should be shorted at a time.

(3) Test conditions are C1 - C4 = 0.1 μF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μF, C2 - C4 = 0.33 μF at V_{CC} = 5 V ± 0.5 V.

6.9 Switching Characteristics: Driver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see [Figure 9-1](#))

PARAMETER		TEST CONDITIONS ⁽³⁾			MIN	TYP ⁽¹⁾	MAX	UNIT
Maximum data rate (See 图 7-1)	R _L = 3 kΩ, One DOUT switching	C _L = 1000 pF			250			kbit/s
		C _L = 250 pF,	V _{CC} = 3 V to 4.5 V		1000			
		C _L = 1000 pF,	V _{CC} = 4.5 V to 5.5 V		1000			
t _{sk(p)}	Pulse skew ⁽²⁾	C _L = 150 pF to 2500 pF,	R _L = 3 kΩ to 7 kΩ,	See 图 7-2	300			ns
SR(tr)	Slew rate, transition region (see 图 7-1)	R _L = 7 kΩ,	C _L = 150 pF to 1000 pF			8	90	V/ μ s
		R _L = 3 kΩ	C _L = 1000 pF			12	60	
			C _L = 150 pF to 250 pF			24	150	

(1) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

(2) Pulse skew is defined as |t_{PLH} - t_{PHL}| of each channel of the same device.

(3) Test conditions are C1 - C4 = 0.1 μF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μF, C2 - C4 = 0.33 μF at V_{CC} = 5 V ± 0.5 V.

6.10 Electrical Characteristics: Receiver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see [Figure 9-1](#))

PARAMETER		TEST CONDITIONS ⁽²⁾	MIN	TYP ⁽¹⁾	MAX	UNIT
V _{OH}	High-level output voltage	I _{OH} = -1 mA	V _{CC} - 0.6	V _{CC} - 0.1		V
V _{OL}	Low-level output voltage	I _{OL} = 1.6 mA			0.4	V
V _{IT+}	Positive-going input threshold voltage	V _{CC} = 3.3 V		1.5	2.4	V
		V _{CC} = 5 V		1.8	2.4	
V _{IT-}	Negative-going input threshold voltage	V _{CC} = 3.3 V	0.6	1.2		V
		V _{CC} = 5 V	0.8	1.5		
V _{hys}	Input hysteresis (V _{IT+} - V _{IT-})			0.3		V
I _{OZ}	Output leakage current	$\overline{\text{EN}} = 1$		±0.05	±10	μA
r _i	Input resistance	V _I = ±3 V to ±25 V	3	5	7	kΩ

(1) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

(2) Test conditions are C1 - C4 = 0.1 μF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μF, C2 - C4 = 0.33 μF at V_{CC} = 5 V ± 0.5 V.

6.11 Switching Characteristics: Receiver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

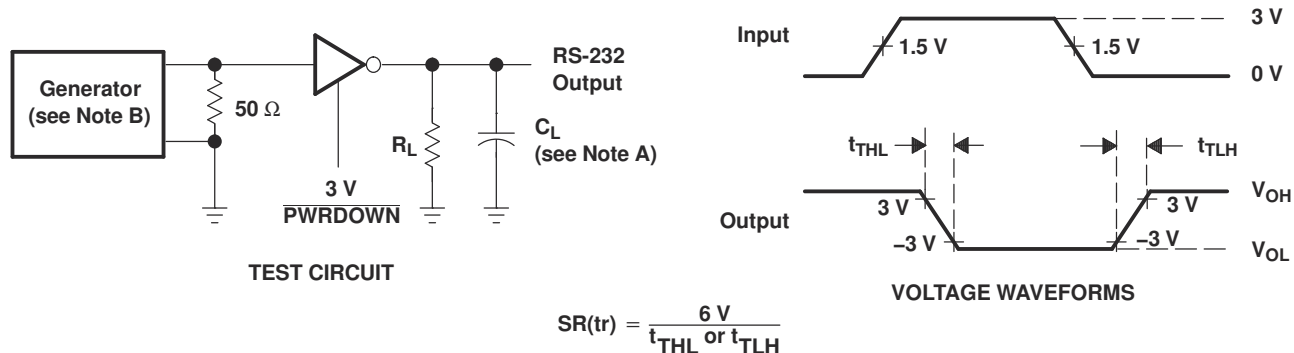
PARAMETER		TEST CONDITIONS ⁽³⁾	TYP ⁽¹⁾	UNIT
t _{PLH}	Propagation delay time, low- to high-level output	C _L = 150 pF, See Figure 7-3	300	ns
t _{PHL}	Propagation delay time, high- to low-level output	C _L = 150 pF, See Figure 7-3	300	ns
t _{en}	Output enable time	C _L = 150 pF, R _L = 3 kΩ, See Figure 7-4	200	ns
t _{dis}	Output disable time	C _L = 150 pF, R _L = 3 kΩ, See Figure 7-4	200	ns
t _{sk(p)}	Pulse skew ⁽²⁾	See Figure 7-3	300	ns

(1) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

(2) Pulse skew is defined as |t_{PLH} - t_{PHL}| of each channel of the same device.

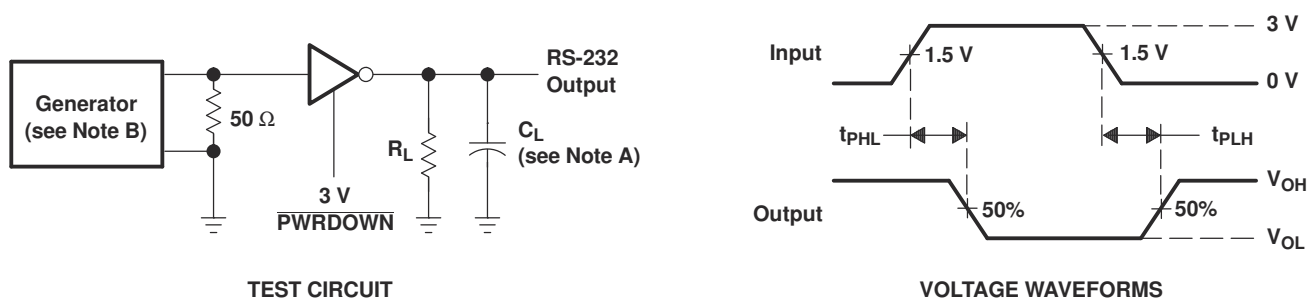
(3) Test conditions are C1 - C4 = 0.1 μF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μF, C2 - C4 = 0.33 μF at V_{CC} = 5 V ± 0.5 V.

7 Parameter Measurement Information



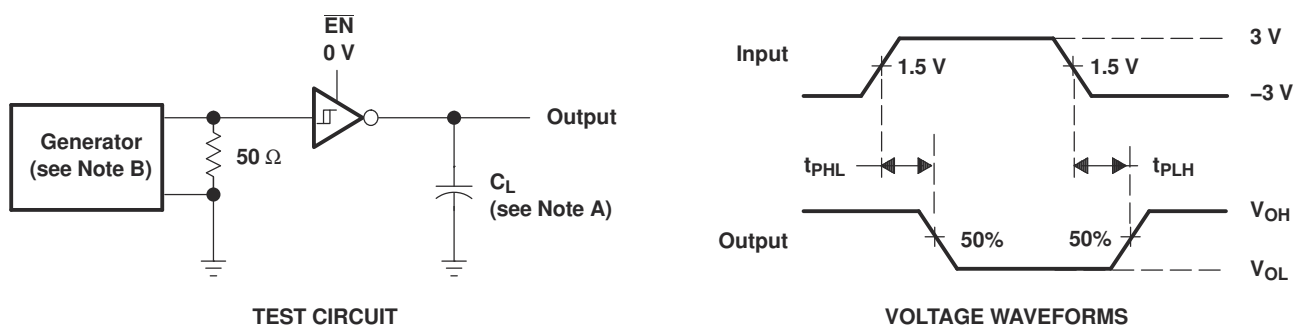
- A. C_L includes probe and jig capacitance.
- B. The pulse generator has the following characteristics: PRR = 250 kbit/s, $Z_O = 50\ \Omega$, 50% duty cycle, $t_r \leq 10\text{ ns}$, $t_f \leq 10\text{ ns}$.

图 7-1. Driver Slew Rate



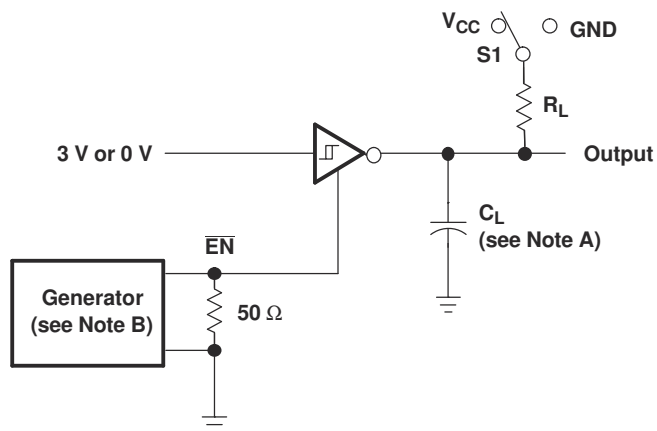
- A. C_L includes probe and jig capacitance.
- B. The pulse generator has the following characteristics: PRR = 250 kbit/s, $Z_O = 50\ \Omega$, 50% duty cycle, $t_r \leq 10\text{ ns}$, $t_f \leq 10\text{ ns}$.

图 7-2. Driver Pulse Skew

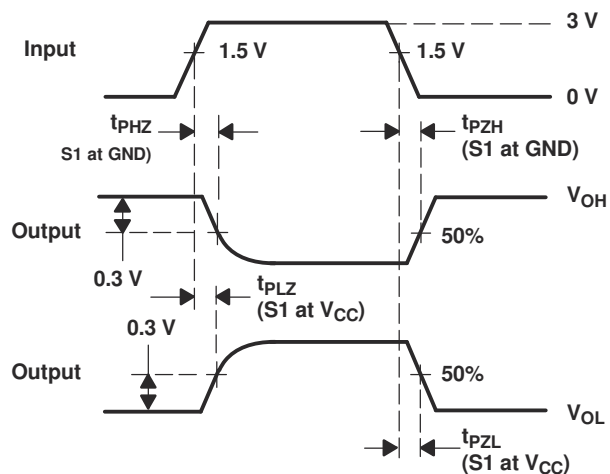


- A. C_L includes probe and jig capacitance.
- B. The pulse generator has the following characteristics: $Z_O = 50\ \Omega$, 50% duty cycle, $t_r \leq 10\text{ ns}$, $t_f \leq 10\text{ ns}$.

图 7-3. Receiver Propagation Delay Times



TEST CIRCUIT



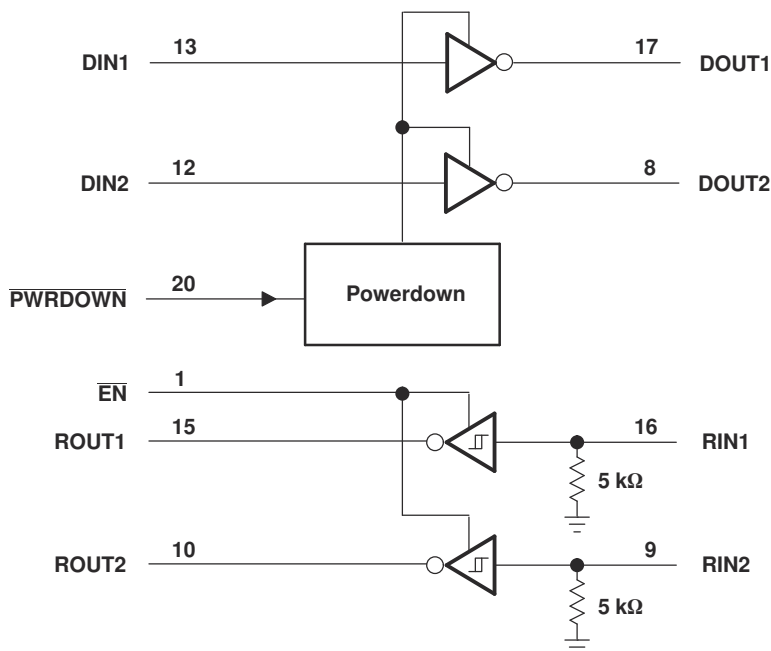
VOLTAGE WAVEFORMS

- A. C_L includes probe and jig capacitance.
- B. The pulse generator has the following characteristics: $Z_O = 50\ \Omega$, 50% duty cycle, $t_r \leq 10\text{ ns}$, $t_f \leq 10\text{ ns}$.

图 7-4. Receiver Enable and Disable Times

8 Detailed Description

8.1 Functional Block Diagram



Pin numbers are for the DB, DW, and PW packages.

图 8-1. Logic Diagram (Positive Logic)

8.2 Device Functional Modes

表 8-1. Function Tables: Each Driver

INPUTS ⁽¹⁾		OUTPUT DOUT
DIN	PWRDOWN	
X	L	Z
L	H	H
H	H	L

(1) H = high level, L = low level, X = irrelevant, Z = high impedance

表 8-2. Function Table: Each Receiver

INPUTS ⁽¹⁾		OUTPUT ROUT
RIN	EN	
L	L	H
H	L	L
X	H	Z
Open	L	H

(1) H = high level, L = low level, X = irrelevant,
Z = high impedance (off),
Open = input disconnected or connected driver off

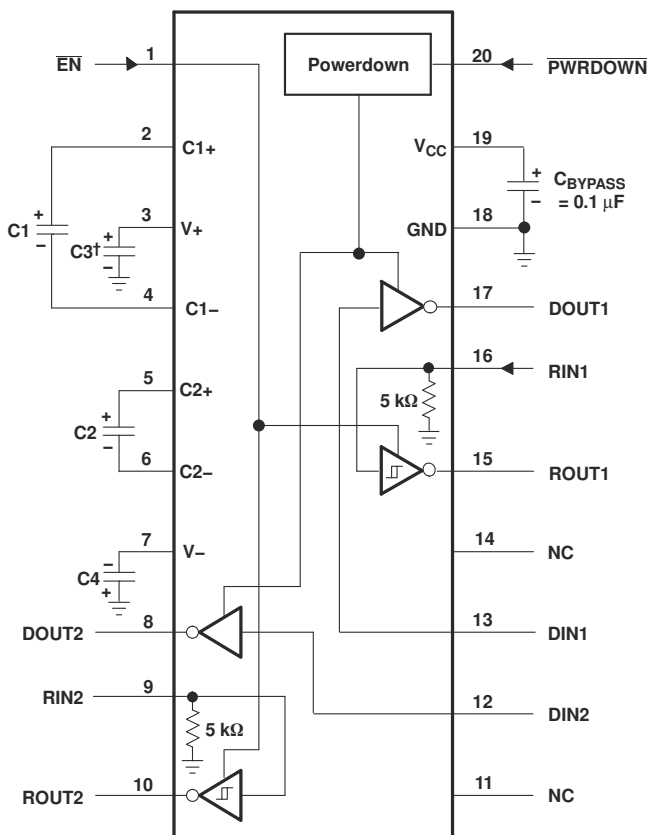
9 Application and Implementation

Note

以下应用部分中的信息不属于 TI 器件规格的范围，TI 不担保其准确性和完整性。TI 的客户应负责确定器件是否适用于其应用。客户应验证并测试其设计，以确保系统功能。

9.1 Application Information

9.2 Typical Application



† C3 can be connected to V_{CC} or GND.

NOTES: A. Resistor values shown are nominal.

B. NC – No internal connection

C. Nonpolarized ceramic capacitors are acceptable. If polarized tantalum or electrolytic capacitors are used, they should be connected as shown.

V_{CC} vs CAPACITOR VALUES

V_{CC}	C1	C2, C3, and C4
3.3 V $\pm$ 0.3 V	0.1 μ F	0.1 μ F
5 V $\pm$ 0.5 V	0.047 μ F	0.33 μ F
3 V to 5.5 V	0.1 μ F	0.47 μ F

图 9-1. Typical Operating Circuit and Capacitor Values

10 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

10.1 接收文档更新通知

要接收文档更新通知，请导航至 ti.com 上的器件产品文件夹。点击 [订阅更新](#) 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

10.2 支持资源

TI E2E™ 支持论坛是工程师的重要参考资料，可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的《使用条款》。

10.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.

所有商标均为其各自所有者的财产。

10.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

10.5 术语表

TI 术语表 本术语表列出并解释了术语、首字母缩略词和定义。

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
SN65C3222EDB	Active	Production	SSOP (DB) 20	70 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MU222E
SN65C3222EDB.A	Active	Production	SSOP (DB) 20	70 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MU222E
SN65C3222EDBR	Active	Production	SSOP (DB) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MU222E
SN65C3222EDBR.A	Active	Production	SSOP (DB) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MU222E
SN65C3222EDW	Active	Production	SOIC (DW) 20	25 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3222E
SN65C3222EDW.A	Active	Production	SOIC (DW) 20	25 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3222E
SN65C3222EDWR	Active	Production	SOIC (DW) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3222E
SN65C3222EDWR.A	Active	Production	SOIC (DW) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3222E
SN65C3222EPWR	NRND	Production	TSSOP (PW) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MU222E
SN65C3222EPWR.A	NRND	Production	TSSOP (PW) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MU222E
SN75C3222EPW	Obsolete	Production	TSSOP (PW) 20	-	-	Call TI	Call TI	0 to 70	MY222E

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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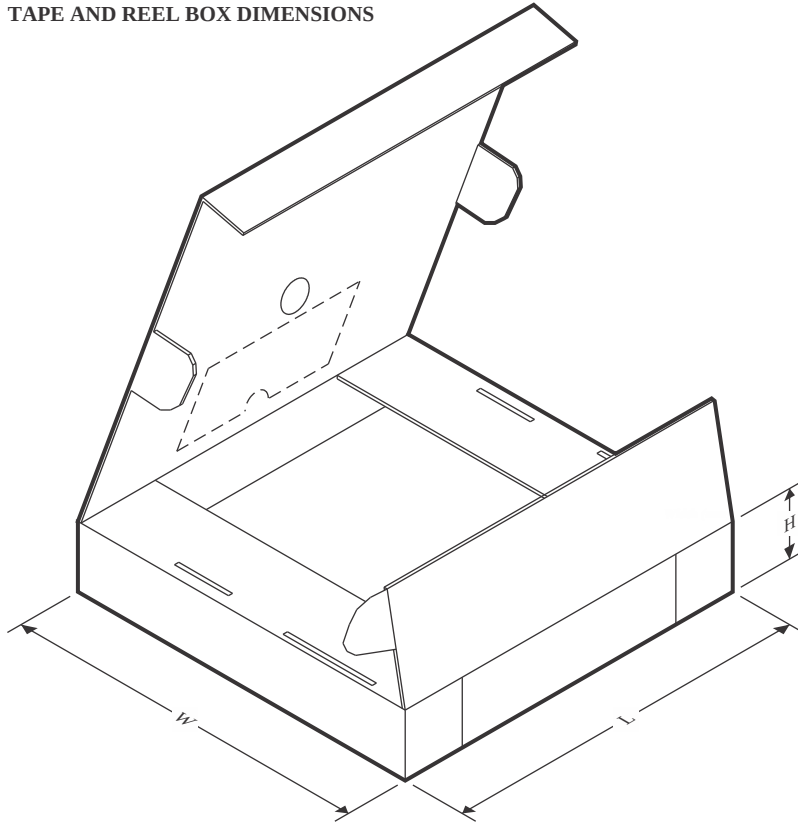
TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65C3222EDBR	SSOP	DB	20	2000	330.0	16.4	8.2	7.5	2.5	12.0	16.0	Q1
SN65C3222EDWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
SN65C3222EPWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

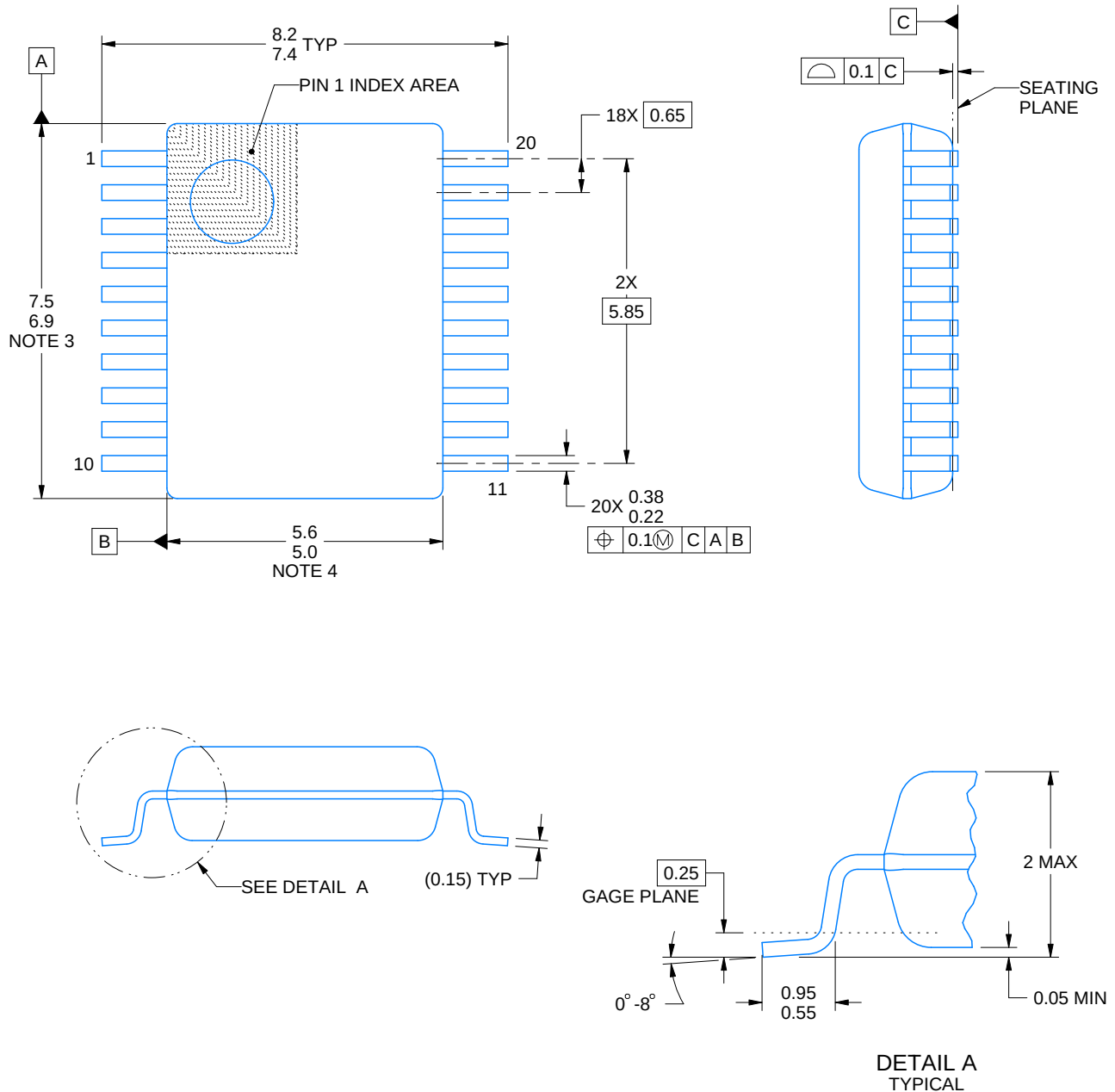
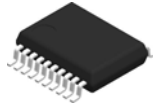
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65C3222EDBR	SSOP	DB	20	2000	353.0	353.0	32.0
SN65C3222EDWR	SOIC	DW	20	2000	356.0	356.0	45.0
SN65C3222EPWR	TSSOP	PW	20	2000	353.0	353.0	32.0

TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
SN65C3222EDB	DB	SSOP	20	70	530	10.5	4000	4.1
SN65C3222EDB.A	DB	SSOP	20	70	530	10.5	4000	4.1
SN65C3222EDW	DW	SOIC	20	25	507	12.83	5080	6.6
SN65C3222EDW.A	DW	SOIC	20	25	507	12.83	5080	6.6



4214851/B 08/2019

NOTES:

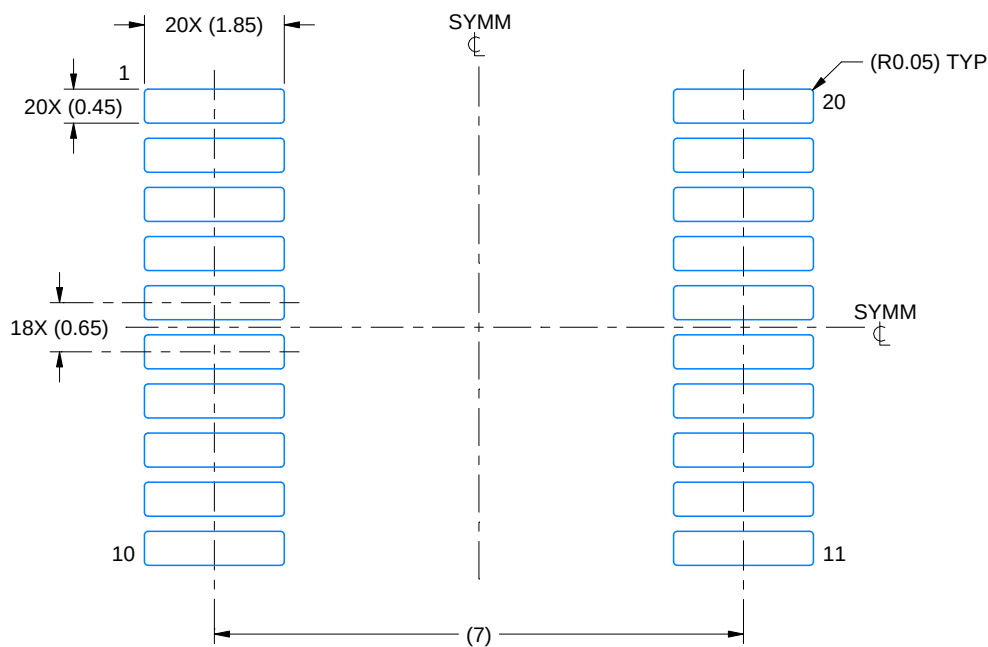
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-150.

EXAMPLE BOARD LAYOUT

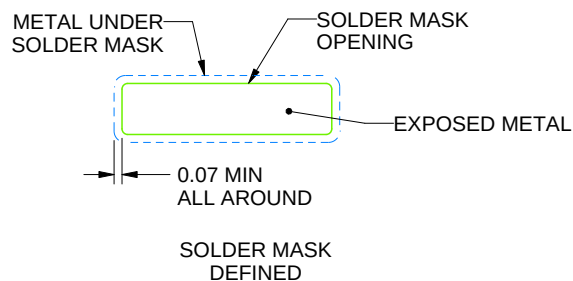
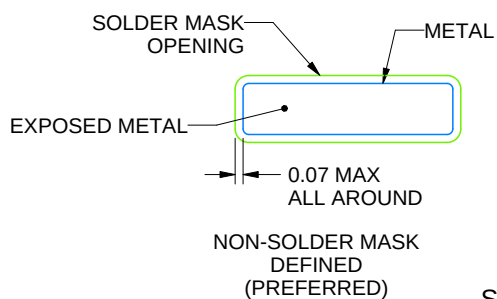
DB0020A

SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X



SOLDER MASK DETAILS

4214851/B 08/2019

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

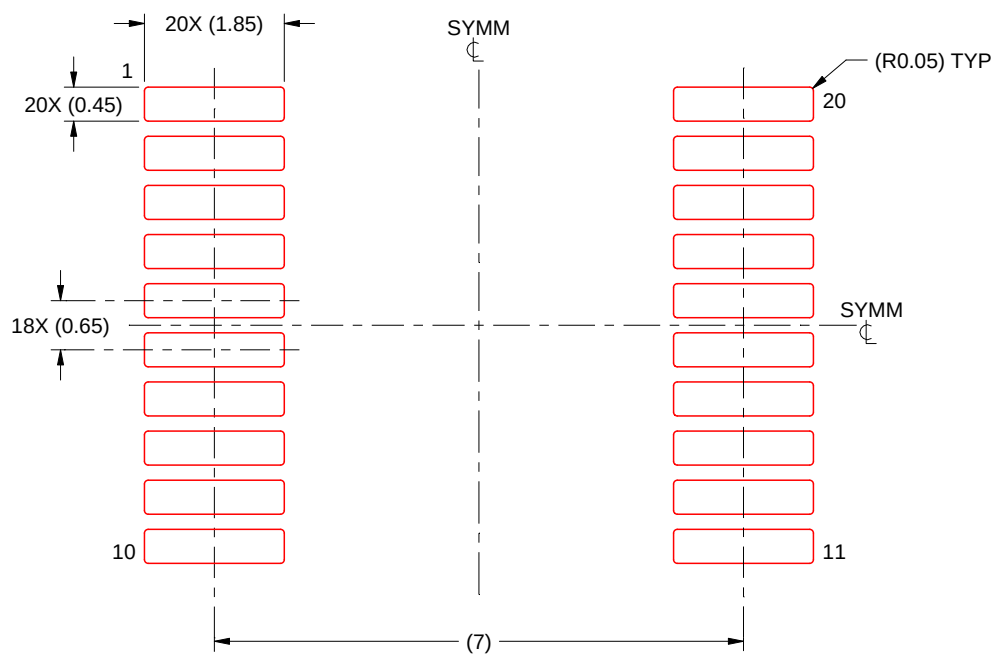
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DB0020A

SSOP - 2 mm max height

SMALL OUTLINE PACKAGE

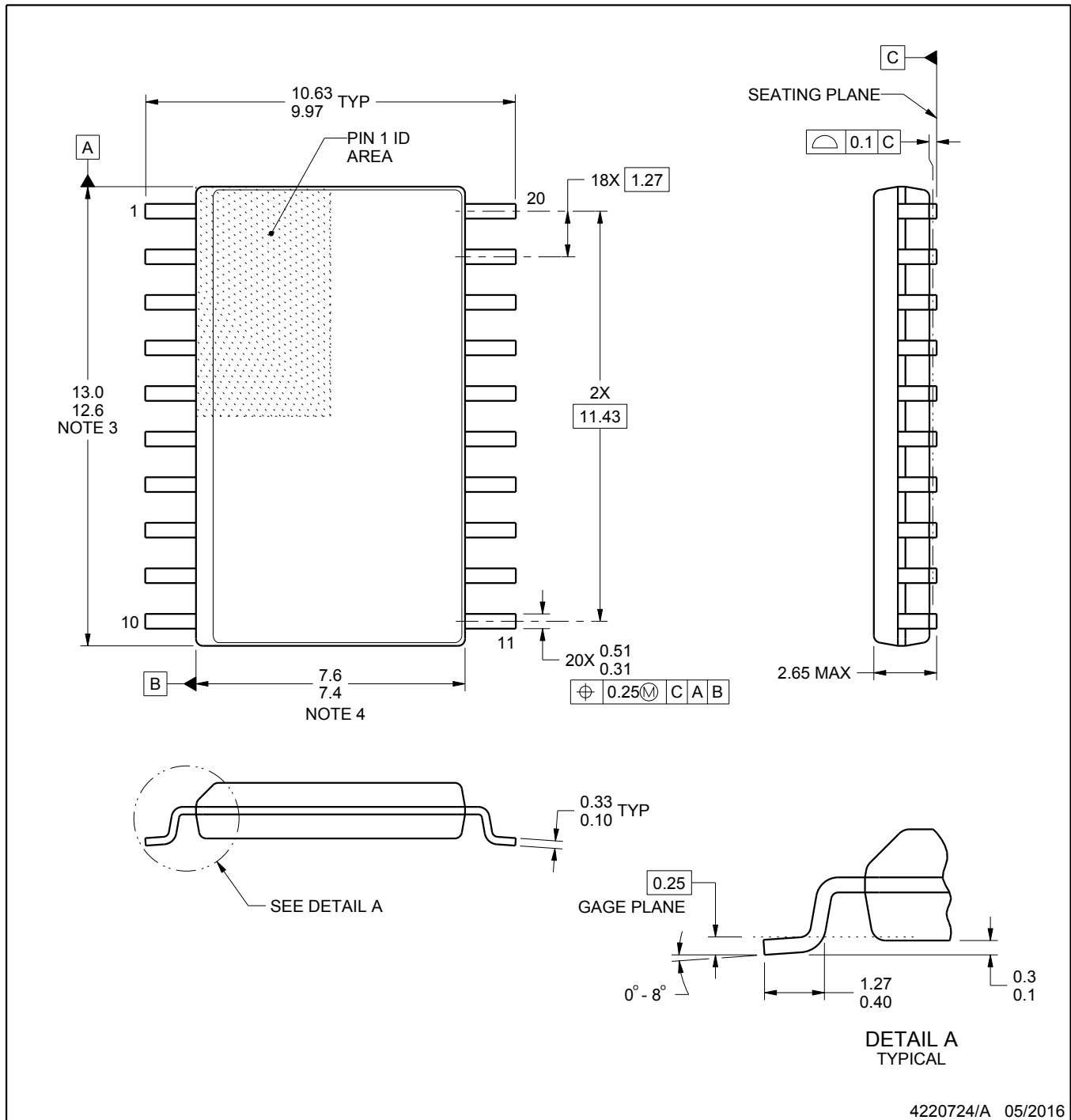
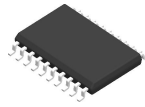


SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4214851/B 08/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.



NOTES:

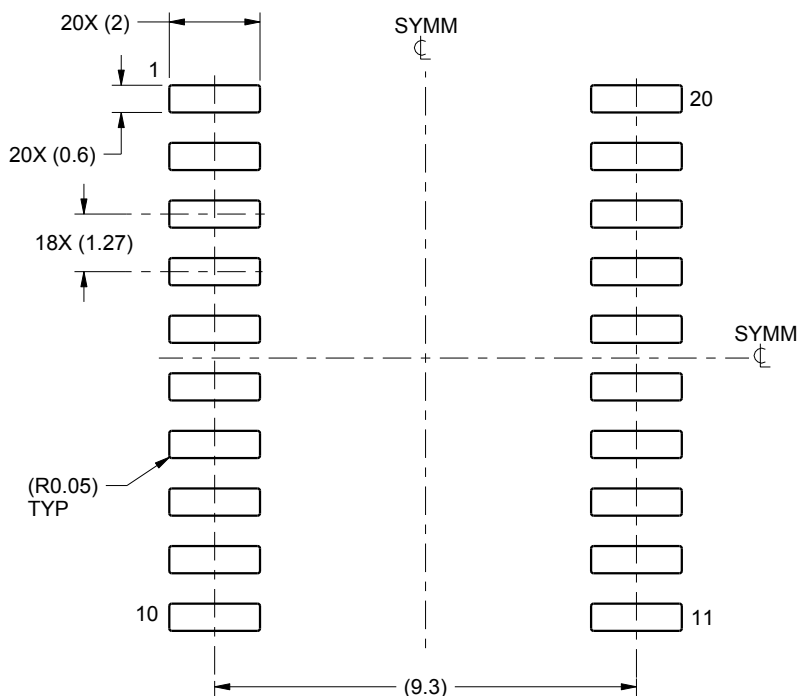
1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
5. Reference JEDEC registration MS-013.

EXAMPLE BOARD LAYOUT

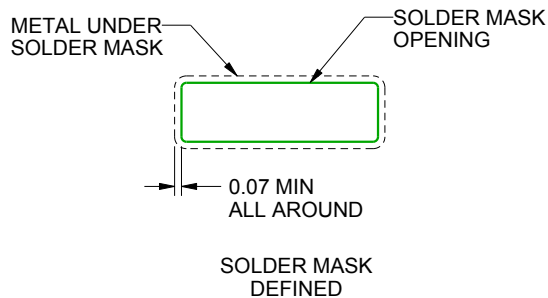
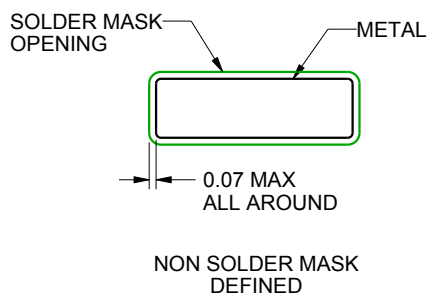
DW0020A

SOIC - 2.65 mm max height

SOIC



LAND PATTERN EXAMPLE
SCALE:6X



SOLDER MASK DETAILS

4220724/A 05/2016

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

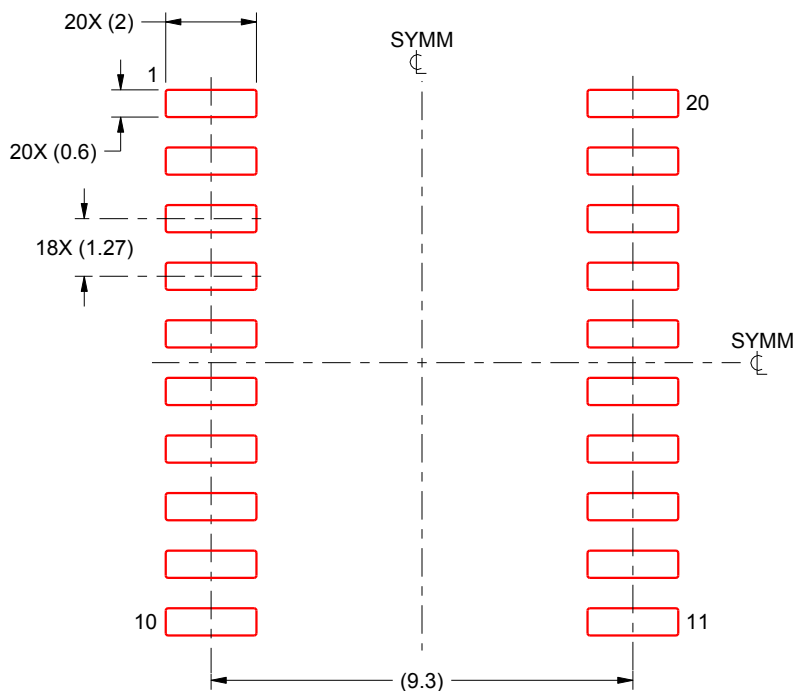
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DW0020A

SOIC - 2.65 mm max height

SOIC

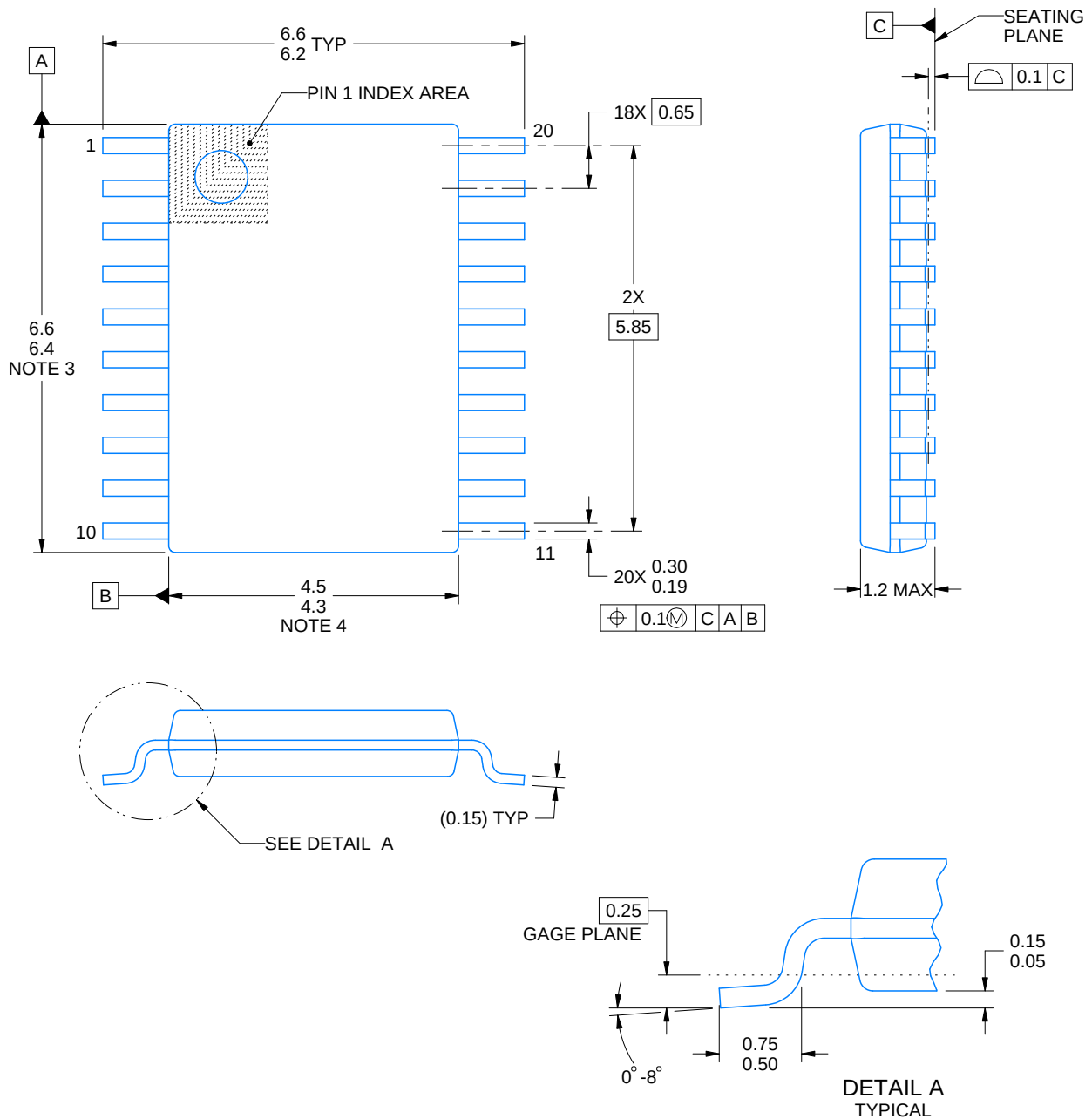
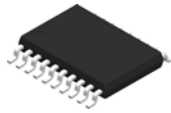


SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:6X

4220724/A 05/2016

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.



4220206/A 02/2017

NOTES:

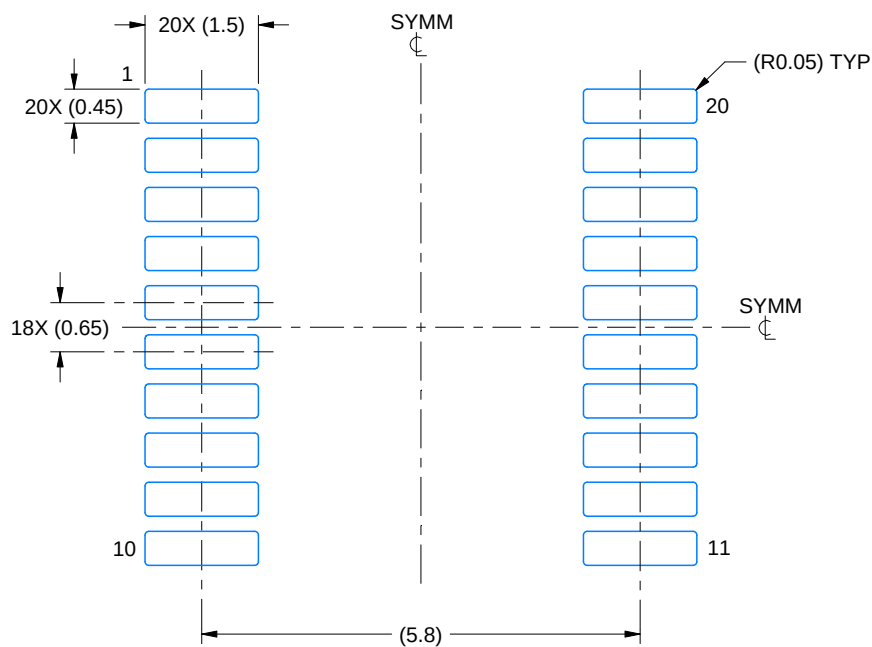
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.

EXAMPLE BOARD LAYOUT

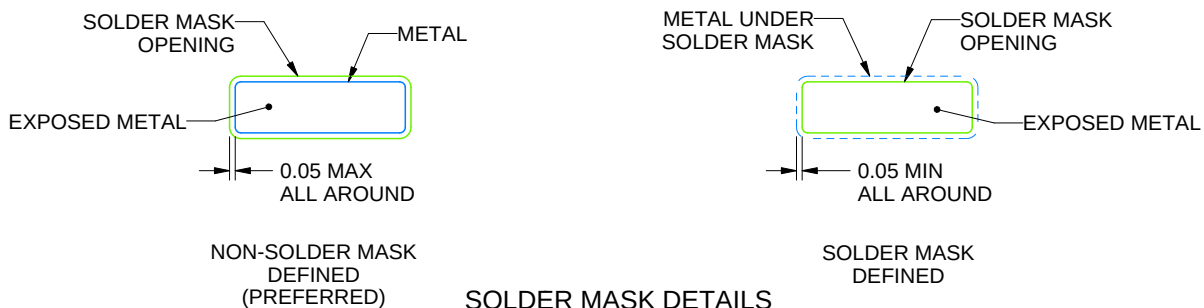
PW0020A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X



4220206/A 02/2017

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

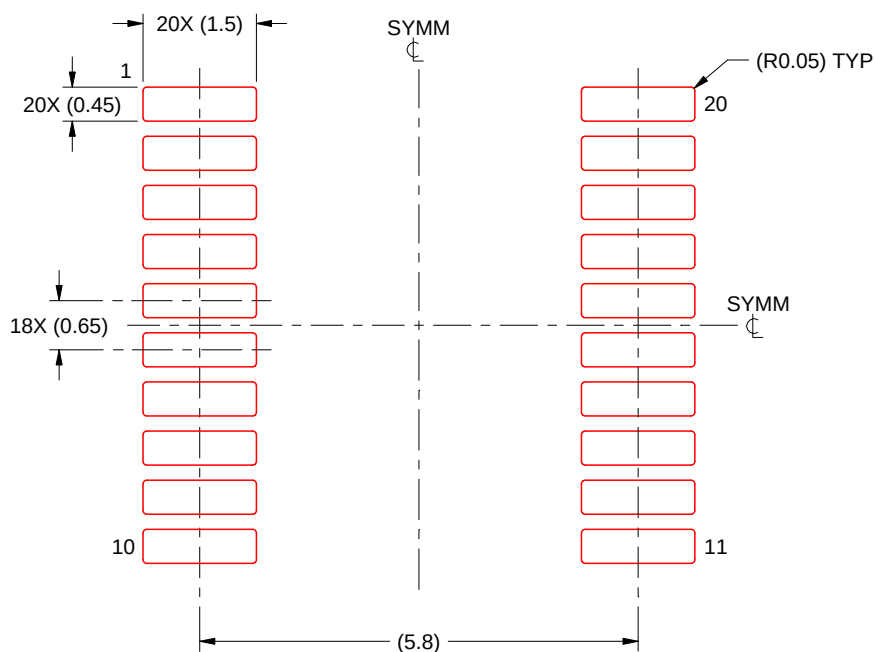
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

PW0020A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220206/A 02/2017

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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